20V N-Channel Enhancement Mode MOSFET

VDS= 20V

RDS(ON), Vgs@ 4.5V, Ids@ 3.0A ＜70mΩ

RDS(ON), Vgs@ 2.5V, Ids@ 2.0A ＜80mΩ

Features

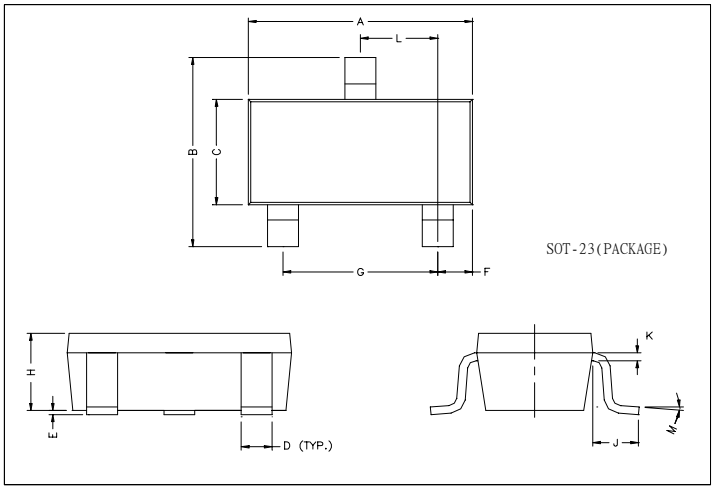
Advanced trench process technology

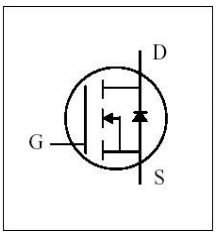
High Density Cell Design For Ultra Low On-Resistance

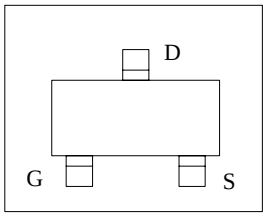
High Power and Current handing capability

Ideal for Li ion battery pack applications

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Maximum Ratings and Thermal Characteristics (TA = 25oC unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current		I_D	2.3	A
Pulsed Drain Current [1]		I_{DM}	8	
Maximum Power Dissipation	TA = 25°C	P_D	1.25	W
	TA = 75°C		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C
Junction-to-Ambient Thermal Resistance (PCB mounted) [2]		$R_{\theta JA}$	78	°C/W

Notes

1) Pulse width limited by maximum junction temperature.

2) Surface Mounted on FR4 Board, t ≤ 5 sec.

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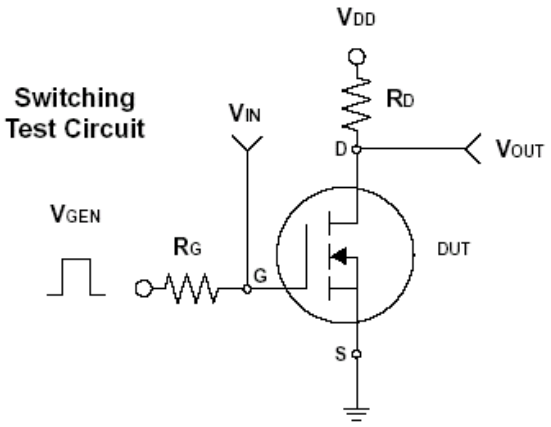
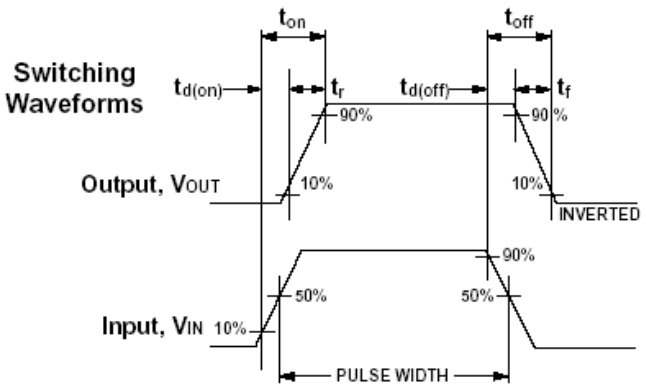
ELECTRICAL CHARACTERISTICS (TA = 25oC unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Miax.	Unit
Static [3]						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250uA	20			V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 2.5V, I_D = 2.0A		70.0	80.0	mΩ
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 3.0A		60.0	70.0	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D = 250uA	0.6	0.76		V
Zero Gate Voltage Drain Current 0	I_{DSS}	V_{DS} = 20V, V_{GS} = 0V			1	uA
Gate Body Leakage	I_{GSS}	V_{GS} = ± 12V, V_{DS} = 0V			±100	nA
Forward Transconductance	g_{fs}	V_{DS} = 5V, I_D = 4.2A		5	__	S
Dynamic[4]						
Total Gate Charge	Q_g	V_{DS} = 10V, I_D = 3.6A V_{GS} = 4.5V		5.4	10	nC
Gate-Source Charge	Q_{gs}			0.65		
Gate-Drain Charge	Q_{gd}			1.5		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10V, R_G = 6Ω I_D = 1A, V_{GS} = 4.5V RL = 5.5Ω		12	25	ns
Turn-On Rise Time	t_r			36	60	
Turn-Off Delay Time	$t_{d(off)}$			34	60	
Turn-Off Fall Time	t_f			10	25	
Input Capacitance	C_{iss}	V_{DS} = 10V, V_{GS} = 0V f = 1.0 MHz		340		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			33		
Source-Drain Diode						
Max. Diode Forward Current	I_S				1.6	A
Diode Forward Voltage	V_{SD}	I_S = 1.6A, V_{GS} = 0V			1.2	V

Notes
3) Short duration test pulse used to minimize self-heating effect.
4) Pulse test pulse width<=300us,duty cycle<= 2%.





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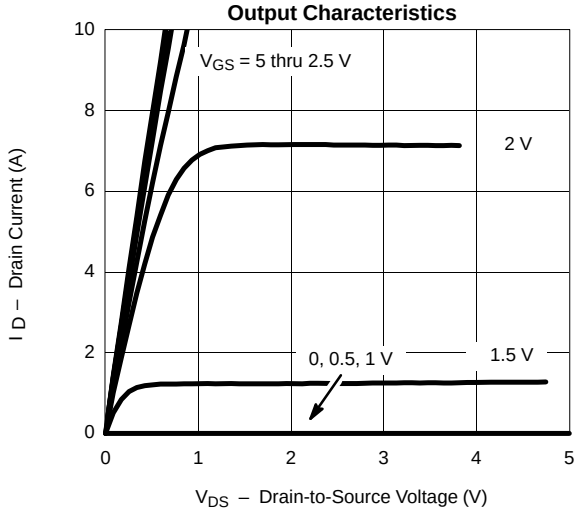
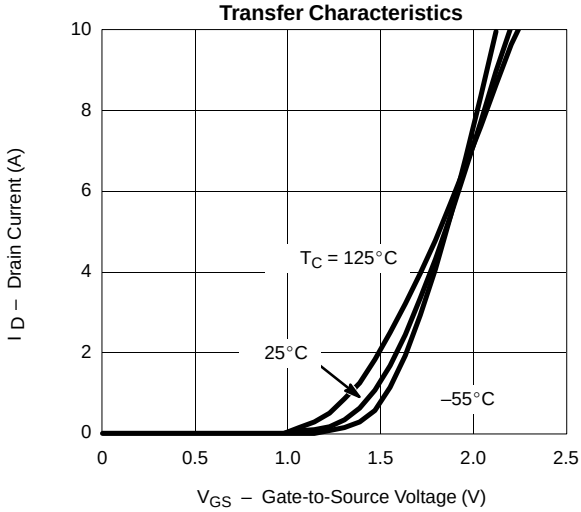
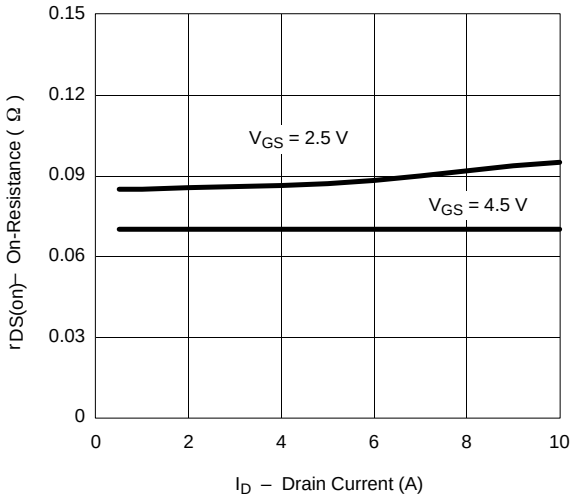
Output Characteristics



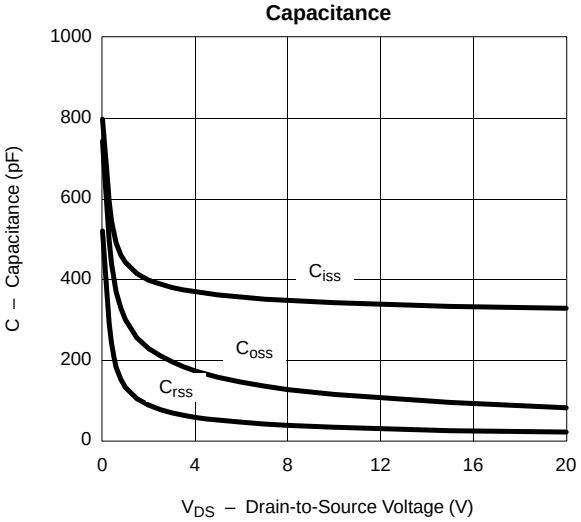
Transfer Characteristics



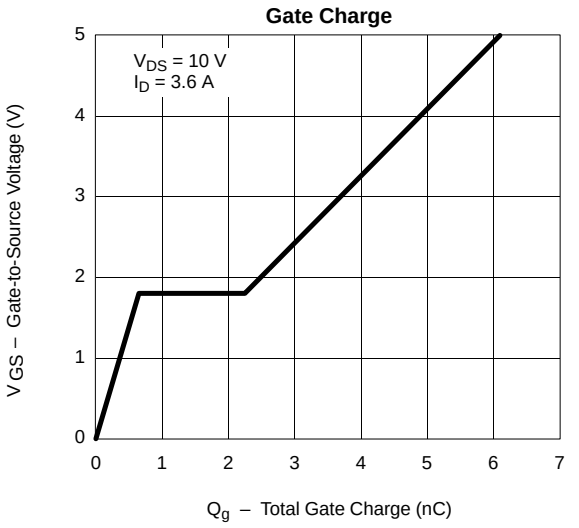
On-Resistance vs. Drain Current



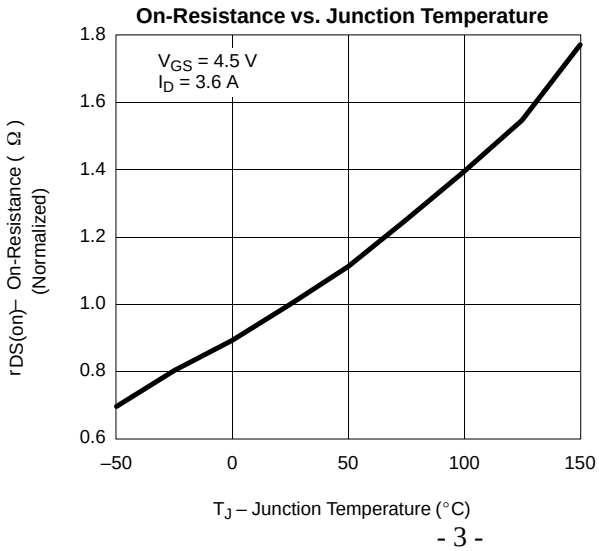
Capacitance



Gate Charge



On-Resistance vs. Junction Temperature



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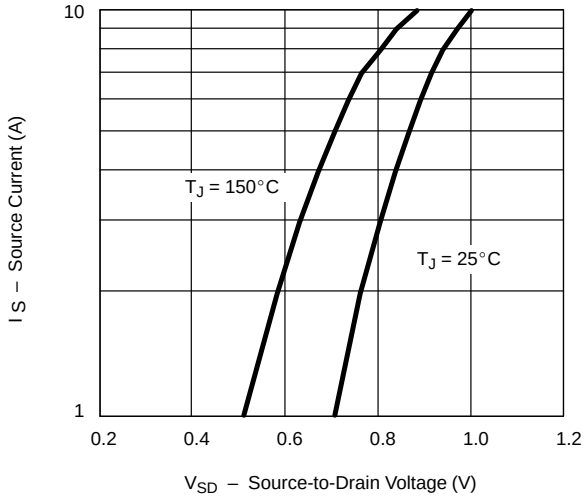
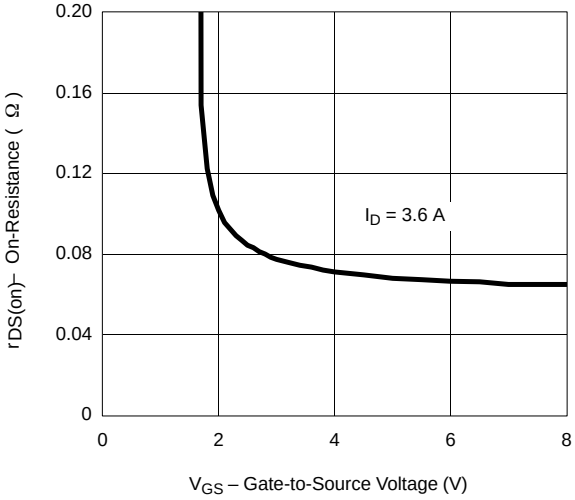
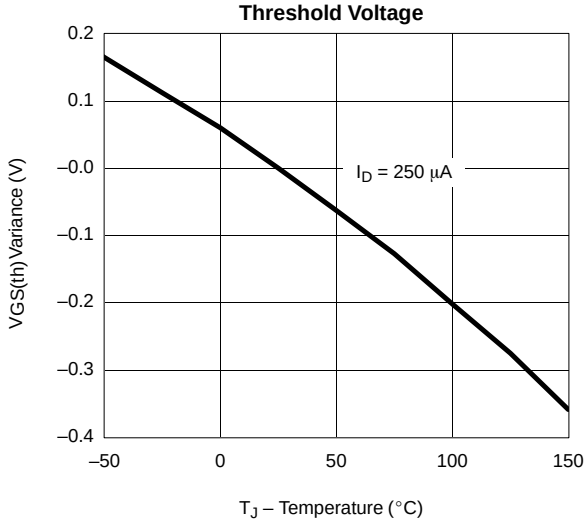
Source-Drain Diode Forward Voltage



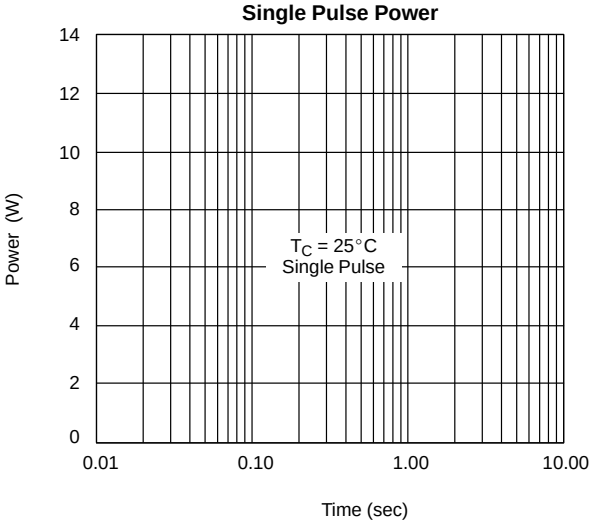
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient